Data Sheet

Central™
Semiconductor Corp.

145 Adams Ave., Hauppauge, NY 11788 USA
Phone (516) 435-1110 FAX (516) 435-1824

Manufacturers of World Class Discrete Semiconductors

CMPF5460
CMPF5461
CMPF5462

SURFACE MOUNT
SILICON P-CHANNEL JFET

SOT-23 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPF5460 Series types are epoxy molded P-Channel Silicon Junction Field Effect Transistor manufactured in an SOT-23 case, designed for low level amplifier applications. **Marking code is 6E, 6E1 and 6E2 respectively.**

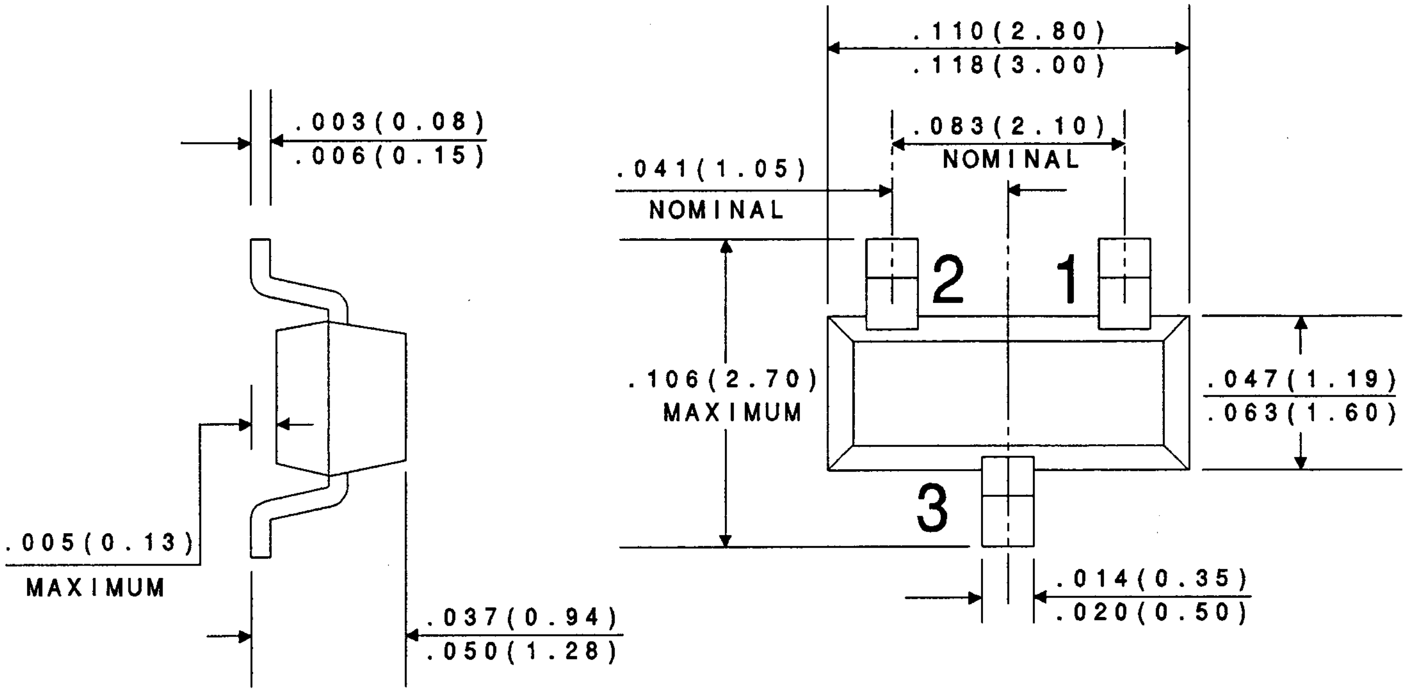
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Gate-Drain Voltage	V_{GD}	40	V
Gate-Source Voltage	V_{GS}	40	V
Gate Current	I_G	10	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

		CMPF5460		CMPF5461		CMPF5462		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	MIN	MAX	UNITS
I_{GSS}	V_{GS}=20V		5.0		5.0		5.0	nA
I_{DSS}	V_{DS}=15V	1.0	5.0	2.0	9.0	4.0	16	mA
BV_{GSS}	I_G=10µA	40		40		40		V
$V_{GS(off)}$	V_{DS}=15V, I_D=1.0nA	0.75	6.0	1.0	7.5	1.8	9.0	V
g_{fs}	V_{DS}=15V, V_{GS}=0, f=1.0kHz	1.0	5.0	1.5	5.5	2.0	6.0	µmhos
C_{iss}	V_{DS}=15V, V_{GS}=0, f=1.0MHz		7.0		7.0		7.0	pF
C_{rss}	V_{DS}=15V, V_{GS}=0, f=1.0MHz		3.0		3.0		3.0	pF
e_N	V_{DS}=15V, V_{GS}=0, f=100Hz	60 TYP.		60 TYP.		60 TYP.		$nV/\sqrt{Hz}$

SOT-23 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm)

LEAD CODE:

1) DRAIN
2) SOURCE
3) GATE

MARKING CODE:

CMPF5460 - 6E
CMPF5461 - 6E1
CMPF5462 - 6E2

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